

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0062C

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
 Top side (Anode) : Aluminum alloy .
 (Cathode) : Aluminum alloy.
 *Back side with SiO₂ covered

3. Size :

- 3-1. Chip size : 63 mils × 63 mils (1.6 mm × 1.6 mm).
- 3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
- 3-3. Active area : 53 mils × 53 mils (1.346 mm × 1.346 mm).
- 3-4. Bonding pad (Anode) : 6 mils × 6 mils (0.153 mm × 0.153 mm).
 (Cathode) : 6 mils × 6 mils (0.153 mm × 0.153 mm).
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
**Reverse dark Current	I _D	V _R =20V Ee=0mW/cm ²			10	nA
**Reverse breakdown voltage	V _{(BR)R}	I _R =100uA Ee=0mW/cm ²	60			V
Open circuit Voltage	V _{oc}	T=2856K Ee=5mW/cm ²		390		mV
Short circuit Current	I _{sc}	T=2856K Ee=5mW/cm ²		12		μA
Reverse light Current	I _L	V _R =5V T=2856K Ee=5mW/cm ²		12		μA
Total Capacitance	C _t	V _R =5V Ee=0mW/cm ² f=1MHz		6		pF

*Based on 100% probing

